



Product Discontinue Notification (PDN)

Date: February 25th, 2022

PDN TRACKING NO: PDN#20220225

Subject:

Product Discontinue Notification (PDN) for **16Mb** Low Power ASRAM and **1Mb** Fast ASRAM.

Affected Part Numbers	<p><u>16Mb Low Power ASRAM:</u></p> <ul style="list-style-type: none"> • AS6C1616-55BIN, AS6C1616-55BINTR • AS6C1616-70BIN, AS6C1616-70BINTR • AS6C1608-55TIN, AS6C1608-55TINTR • AS6C1608-55BIN, AS6C1608-55BINTR <p><u>1Mb FAST ASRAM:</u></p> <ul style="list-style-type: none"> • AS7C31025C-12TIN, AS7C31025C-12TINTR • AS7C31025C-12JIN, AS7C31025C-12JINTR • AS7C31026C-12JIN, AS7C31026C-12JINTR • AS7C31026C-12TIN, AS7C31026C-12TINTR • AS7C31026C-12BIN, AS7C31026C-12BINTR • AS7C1024C-12JIN, AS7C1024C-12JINTR • AS7C1024C-12TJIN, AS7C1024C-12TJINTR • AS7C1025C-15JIN, AS7C1025C-15JINTR • AS7C1026C-15JIN, AS7C1026C-15JINTR • AS7C1026C-15TIN, AS7C1026C-15TINTR
Description of Change:	End-Of-Line of affected Part Numbers
Reason for Change	<ul style="list-style-type: none"> • Very Low demands • Very Long lead times (wafers & lead frame materials)
Traceability, Guidelines	Traceable through marketing part number
Alternative Part	See Table.1
Summary of Alternative	See Table.1

Last Time Buy Date:	May 30 th , 2022
Last Time Ship Date:	Feb 25 th , 2023
Sample Availability Date for Alternative part numbers	Alternative parts already in Mass Production
PCN Effective Date	February 25 th , 2022

*Any orders after 30th May 2022 are Non-Cancelable/Non-Returnable and cannot be changed. Products cannot be returned in stock rotation after this date.



Table 1 – Affected and Alternative Part Numbers

Product	EOL Affected Part Number	Affected Part Product Description	Alternative Part Number
Low Power ASRAM	AS6C1616-55BIN	3V, 16Mb, 1024K x 16, 55ns, 48b TFBGA, Tray	AS6C1616B-55BIN
	AS6C1616-55BINTR	3V, 16Mb, 1024K x 16, 55ns, 48b TFBGA, T&R	AS6C1616B-55BINTR
	AS6C1616-70BIN	3V, 16Mb, 1024K x 16, 70ns, 48b TFBGA, Tray	AS6C1616B-55BIN
	AS6C1616-70BINTR	3V, 16Mb, 1024K x 16, 70ns, 48b TFBGA, T&R	AS6C1616B-55BINTR
	AS6C1608-55TIN	3V, 16Mb, 2048K x 8, 55ns, 44p TSOP II, Tray	AS6C1608B-45TIN
	AS6C1608-55TINTR	3V, 16Mb, 2048K x 8, 55ns, 44p TSOP II, T&R	AS6C1608B-45TINTR
	AS6C1608-55BIN	3V, 16Mb, 2048K x 8, 55ns, 48b TFBGA, Tray	AS6C1608B-45BIN
	AS6C1608-55BINTR	3V, 16Mb, 2048K x 8, 55ns, 48b TFBGA, T&R	AS6C1608B-45BINTR
FAST ASRAM	AS7C31025C-12TIN	3V, 1Mb, 128K x8, 12ns, 32p TSOP, Tray	None
	AS7C31025C-12TINTR	3V, 1Mb, 128K x8, 12ns, 32p TSOP, T&R	None
	AS7C31025C-12JIN	3V, 1Mb, 128K x8, 12ns, 32p SOJ (400mils), Tube	AS7C31025B-12JIN
	AS7C31025C-12JINTR	3V, 1Mb, 128K x8, 12ns, 32p SOJ (400mils), T&R	AS7C31025B-12JINTR
	AS7C31026C-12JIN	3V, 1Mb, 64K x16, 12ns, 44p SOJ, Tube	AS7C31026B-12JIN
	AS7C31026C-12JINTR	3V, 1Mb, 64K x16, 12ns, 44p SOJ, T&R	AS7C31026B-12JINTR
	AS7C31026C-12TIN	3V, 1Mb, 64K x16, 12ns, 44p TSOP II, Tray	AS7C31026B-12TIN
	AS7C31026C-12TINTR	3V, 1Mb, 64K x16, 12ns, 44p TSOP II, T&R	AS7C31026B-12TINTR
	AS7C31026C-12BIN	3V, 1Mb, 64K x16, 12ns, 44p SOJ, Tube	None
	AS7C31026C-12BINTR	3V, 1Mb, 64K x16, 12ns, 44p SOJ, T&R	None
	AS7C1024C-12JIN	5V, 1Mb, 128K x8, 12ns, 32p SOJ (400mils), Tube	AS7C1024B-12JIN
	AS7C1024C-12JINTR	5V, 1Mb, 128K x8, 12ns, 32p SOJ (400mils), T&R	AS7C1024B-12JINTR
	AS7C1024C-12TJIN	5V, 1Mb, 128K x8, 12ns, 32p SOJ (300mils), Tube	AS7C1024B-12TJIN
	AS7C1024C-12TJINTR	5V, 1Mb, 128K x8, 12ns, 32p SOJ (300mils), T&R	AS7C1024B-12TJINTR
	AS7C1025C-15JIN	5V, 1Mb, 128K x8, 15ns, 32p SOJ (400mils), Tube	AS7C1025B-15JIN
	AS7C1025C-15JINTR	5V, 1Mb, 128K x8, 15ns, 32p SOJ (400mils), T&R	AS7C1025B-15JINTR
	AS7C1026C-15JIN	5V, 1Mb, 64K x16, 15ns, 44p SOJ, Tube	AS7C1026B-15JIN
	AS7C1026C-15JINTR	5V, 1Mb, 64K x16, 15ns, 44p SOJ, T&R	AS7C1026B-15JINTR
	AS7C1026C-15TIN	5V, 1Mb, 64K x16, 15ns, 44p TSOP II, Tray	AS7C1026B-15TCN
	AS7C1026C-15TINTR	5V, 1Mb, 64K x16, 15ns, 44p STSOP II, T&R	AS7C1026B-15TCNTR



Alliance Memory Inc.

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Dear Valued Customer:

This letter provides Product Discontinue notification for **16Mb Low Power ASRAM** products “AS6C1616-55BIN/TR”, “AS6C1616-70BIN/TR”, “AS6C1608-55TIN/TR”, “AS6C1608-55BIN/TR” and **1Mb Fast ASRAM** products “AS7C31025C-12TIN/TR” “AS7C31025C-12JIN/TR”, “AS7C31026C-12JIN/TR”, “AS7C31026C-12BIN/TR”, “AS7C31026C-12TIN/TR”, “AS7C1024C-12JIN/TR”, “AS7C1024C-12TJIN/TR”, “AS7C1025C-15JIN/TR”, “AS7C1026C-15JIN/TR” and “AS7C1026C-15TIN/TR” due to very low demands and long lead time issues prevailing in current volatile Market. Alternatives to these products are active and already in mass production. Refer Table.1 for details.

The delivery deadline or last time ship date is **February 25th, 2023** with last time buy (LTB) deadline on **May 30th, 2022**. Please note that the standard shipment dates will apply in general and extended delivery dates must be pre-arranged and accepted in writing by Alliance Memory Management.

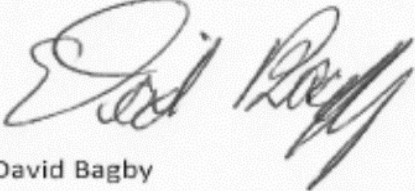
Alliance Memory Inc. will make all reasonable commercial efforts to honor all purchase orders placed before LTB and scheduled delivery dates but reserves the right to not accept new orders or to cancel existing orders if they cannot be fulfilled.

Samples for Alternative part numbers as listed in Table.1 are available for customers to start verification or qualification procedures.

We provide product comparisons within the pages that follow this PDN.

Please contact your local Alliance Memory representative if you have any questions regarding this information.

Yours faithfully



David Bagby
President
Alliance Memory Inc.



AS6C1616-55BIN/TR & AS6C1616B-55BIN/TR Comparison

Parameter	AS6C1616-55BIN/TR	AS6C1616B-55BIN/TR	Comments
Product Description	Low Power ASRAM Rev.0	Low Power ASRAM Rev.B	
Fab / Process Technology	GF / 150nm	HHGSMC / 90nm	
Capacity / Density	16Mb	16Mb	Same
Memory Organization	1024K x 16bits	1024K x 16bits	Same
Operating Power Supply	V _{CC} = 2.7V ~ 3.6V	V _{CC} = 2.7V ~ 3.6V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	CIO: 8pf (Max.)	CIO: 8pf (Max.)	Same
Read Cycle Time (tRC)	55ns (Min.)	55ns (Min.)	Same
Write Cycle Time (tWC)	55ns (Min.)	55ns (Min.)	Same
Addr Access Time(tAA)	55ns (Max.)	55ns (Max.)	Same
OE Access Time (tOE)	30ns (Max.)	30ns (Max.)	Same
V _{OH} (V) @ -1.0mA	2.2 (Min.)	2.2 (Min.)	Same
V _{OL} (V) @ 2mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.2 (Min.)	2.2 (Min.)	Same
V _{IL} (V)	0.6 (Max.)	0.6 (Max.)	Same
I _{LI} / I _{LO} (uA)	1 (Max.)	1 (Max.)	Same
Operating. Current (55ns)	I _{CC} = 60mA	I _{CC} = 18mA	Rev.B better
Operating. Current (1us)	I _{CC1} = 16mA (Max.)	I _{CC1} = 5mA (Max.)	Rev.B better
Standby Current I _{SB1}	40uA (Max.)	40uA (Max.)	Same
V _{DR}	1.2 (Min.)	1.5V (Min.)	Comparable
Package	48b TFBGA	48b TFBGA	Same
Package Outer Dimensions	6mm x 8mm	6mm x 8mm	Same
Ball pitch and array	0.75mm, 3.75 x 5.25mm	0.75mm, 3.75 x 5.25mm	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same

	AS6C1616-55BIN	AS6C1616B-xxBIN
A	LB# OE# A0 A1 A2 CE2	LB# OE# A0 A1 A2 CE2
B	DQ8 UB# A3 A4 CE# DQ0	DQ8 UB# A3 A4 CE# DQ0
C	DQ9 DQ10 A5 A6 DQ1 DQ2	DQ9 DQ10 A5 A6 DQ1 DQ2
D	Vss DQ11 A17 A7 DQ3 Vcc	Vss DQ11 A17 A7 DQ3 Vcc
E	Vcc DQ12 NC A16 DQ4 Vss	Vcc DQ12 NC A16 DQ4 Vss
F	DQ14 DQ13 A14 A15 DQ5 DQ6	DQ14 DQ13 A14 A15 DQ5 DQ6
G	DQ15 A19 A12 A13 WE# DQ7	DQ15 A19 A12 A13 WE# DQ7
H	A18 A8 A9 A10 A11 NC	A18 A8 A9 A10 A11 NC
	1 2 3 4 5 6	1 2 3 4 5 6

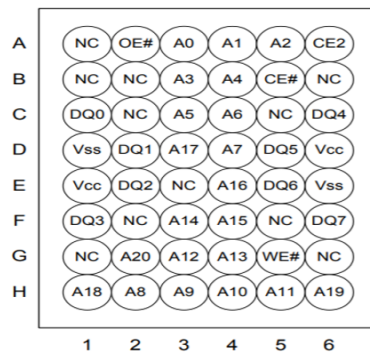
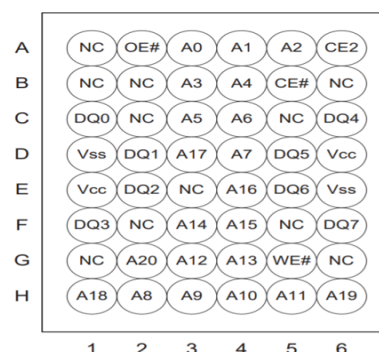
AS6C1616-70BIN/TR & AS6C1616B-55BIN/TR Comparison

Parameter	AS6C1616-70BIN/TR	AS6C1616B-55BIN/TR	Comments
Product Description	Low Power ASRAM Rev.0	Low Power ASRAM Rev.B	
Fab / Process Technology	GF / 150nm	HHGSMC / 90nm	
Capacity / Density	16Mb	16Mb	Same
Memory Organization	1024K x 16bits	1024K x 16bits	Same
Operating Power Supply	V _{CC} = 2.7V ~ 3.6V	V _{CC} = 2.7V ~ 3.6V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	CIO: 8pf (Max.)	CIO: 8pf (Max.)	Same
Read Cycle Time (tRC)	70ns (Min.)	55ns (Min.)	Rev.B better
Write Cycle Time (tWC)	70ns (Min.)	55ns (Min.)	Rev.B better
Addr Access Time(tAA)	70ns (Max.)	55ns (Max.)	Rev.B better
OE Access Time (tOE)	35ns (Max.)	30ns (Max.)	Rev.B better
V _{OH} (V) @ -1.0mA	2.2 (Min.)	2.2 (Min.)	Same
V _{OL} (V) @ 2mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.2 (Min.)	2.2 (Min.)	Same
V _{IL} (V)	0.6 (Max.)	0.6 (Max.)	Same
I _{LI} / I _{LO} (uA)	1 (Max.)	1 (Max.)	Same
Operating. Current	I _{CC} = 45mA (70ns)	I _{CC} = 18mA (55ns)	Rev.B better
Operating. Current (1us)	I _{CC1} = 16mA (Max.)	I _{CC1} = 5mA (Max.)	Rev.B better
Standby Current I _{SB1}	40uA (Max.)	40uA (Max.)	Same
V _{DR}	1.2 (Min.)	1.5V (Min.)	Comparable
Package	48b TFBGA	48b TFBGA	Same
Package Outer Dimensions	6mm x 8mm	6mm x 8mm	Same
Ball pitch and array	0.75mm, 3.75 x 5.25mm	0.75mm, 3.75 x 5.25mm	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same

	AS6C1616-70BIN	AS6C1616B-xxBIN
A	LB# OE# A0 A1 A2 CE2	LB# OE# A0 A1 A2 CE2
B	DQ8 UB# A3 A4 CE# DQ0	DQ8 UB# A3 A4 CE# DQ0
C	DQ9 DQ10 A5 A6 DQ1 DQ2	DQ9 DQ10 A5 A6 DQ1 DQ2
D	Vss DQ11 A17 A7 DQ3 Vcc	Vss DQ11 A17 A7 DQ3 Vcc
E	Vcc DQ12 NC A16 DQ4 Vss	Vcc DQ12 NC A16 DQ4 Vss
F	DQ14 DQ13 A14 A15 DQ5 DQ6	DQ14 DQ13 A14 A15 DQ5 DQ6
G	DQ15 A19 A12 A13 WE# DQ7	DQ15 A19 A12 A13 WE# DQ7
H	A18 A8 A9 A10 A11 NC	A18 A8 A9 A10 A11 NC
	1 2 3 4 5 6	1 2 3 4 5 6

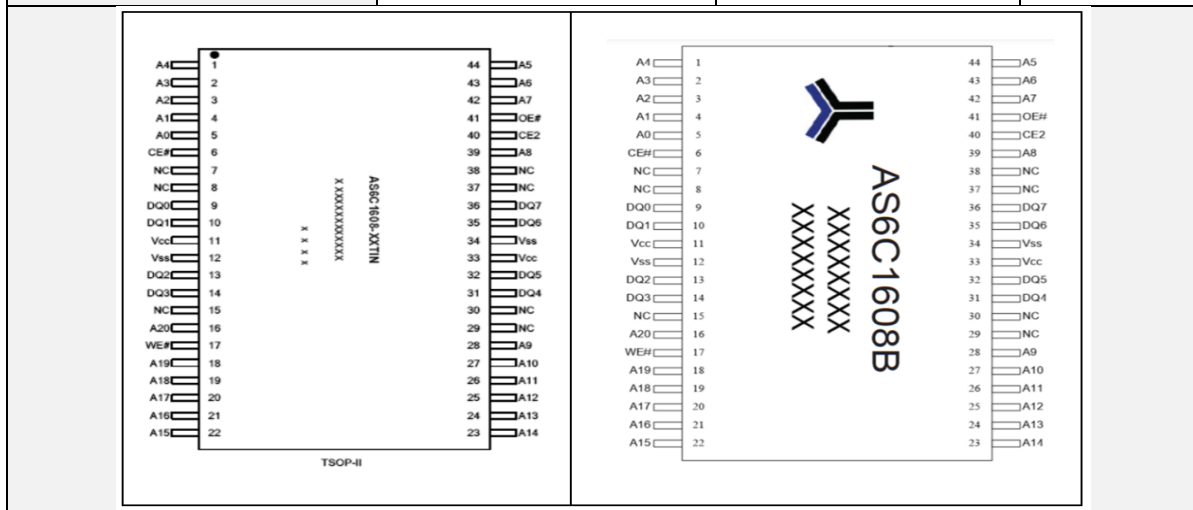
AS6C1608-55BIN/TR & AS6C1608B-45BIN/TR Comparison

Parameter	AS6C1608-55BIN/TR	AS6C1608B-45BIN/TR	Comments
Product Description	Low Power ASRAM Rev.0	Low Power ASRAM Rev.B	
Fab / Process Technology	GF / 150nm	HHGSMC / 90nm	
Capacity / Density	16Mb	16Mb	Same
Memory Organization	2048K x 8bits	2048K x 8bits	Same
Operating Power Supply	V _{CC} = 2.7V ~ 3.6V	V _{CC} = 2.7V ~ 3.6V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	CIO: 8pf (Max.)	CIO: 8pf (Max.)	Same
Read Cycle Time (tRC)	55ns (Min.)	45ns (Min.)	Rev.B better
Write Cycle Time (tWC)	55ns (Min.)	45ns (Min.)	Rev.B better
Addr Access Time(tAA)	55ns (Max.)	45ns (Max.)	Rev.B better
OE Access Time (tOE)	30ns (Max.)	25ns (Max.)	Rev.B better
V _{OH} (V) @ -1.0mA	2.2 (Min.)	2.2 (Min.)	Same
V _{OL} (V) @ 2mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.2 (Min.)	2.2 (Min.)	Same
V _{IL} (V)	0.6 (Max.)	0.6 (Max.)	Same
I _{LI} / I _{LO} (uA)	1 (Max.)	1 (Max.)	Same
Operating. Current	I _{CC} = 60mA (55ns)	I _{CC} = 20mA (45ns)	Rev.B better
Operating. Current (1us)	I _{CC1} = 16mA (Max.)	I _{CC1} = 5mA (Max.)	Rev.B better
Standby Current I _{SB1}	40uA (Max.)	20uA (Max.)	Rev.B better
V _{DR}	1.2 (Min.)	1.5V (Min.)	Comparable
Package	48b TFBGA	48b TFBGA	Same
Package Outer Dimensions	8mm x 10mm	6mm x 8mm	Comparable
Ball pitch and array	0.75mm, 3.75 x 5.25mm	0.75mm, 3.75 x 5.25mm	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same

AS6C1608

AS6C1608B


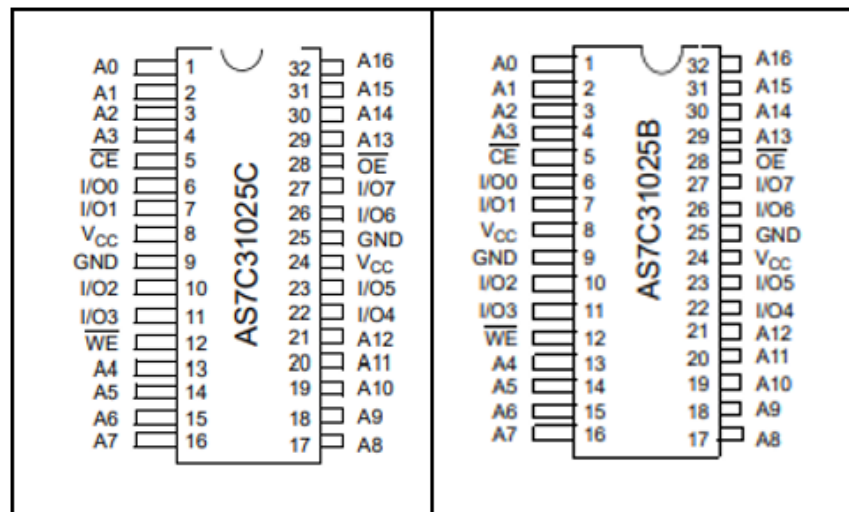
AS6C1608-55TIN/TR & AS6C1608B-45TIN/TR Comparison

Parameter	AS6C1608-55TIN/TR	AS6C1608B-45TIN/TR	Comments
Product Description	Low Power ASRAM Rev.0	Low Power ASRAM Rev.B	
Fab / Process Technology	GF / 150nm	HHGSMC / 90nm	
Capacity / Density	16Mb	16Mb	Same
Memory Organization	2048K x 8bits	2048K x 8bits	Same
Operating Power Supply	V _{CC} = 2.7V ~ 3.6V	V _{CC} = 2.7V ~ 3.6V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	CIO: 8pf (Max.)	CIO: 8pf (Max.)	Same
Read Cycle Time (tRC)	55ns (Min.)	45ns (Min.)	Rev.B better
Write Cycle Time (tWC)	55ns (Min.)	45ns (Min.)	Rev.B better
Addr Access Time(tAA)	55ns (Max.)	45ns (Max.)	Rev.B better
OE Access Time (tOE)	30ns (Max.)	25ns (Max.)	Rev.B better
V _{OH} (V) @ -1.0mA	2.2 (Min.)	2.2 (Min.)	Same
V _{OL} (V) @ 2mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.2 (Min.)	2.2 (Min.)	Same
V _{IL} (V)	0.6 (Max.)	0.6 (Max.)	Same
I _{LI} / I _{LO} (uA)	1 (Max.)	1 (Max.)	Same
Operating. Current	I _{CC} = 60mA (55ns)	I _{CC} = 20mA (45ns)	Rev.B better
Operating. Current (1us)	I _{CC1} = 16mA (Max.)	I _{CC1} = 5mA (Max.)	Rev.B better
Standby Current I _{SB1}	40uA (Max.)	20uA (Max.)	Rev.B better
V _{DR}	1.2 (Min.)	1.5V (Min.)	Comparable
Package	44pin TSOP II	44pin TSOP II	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same



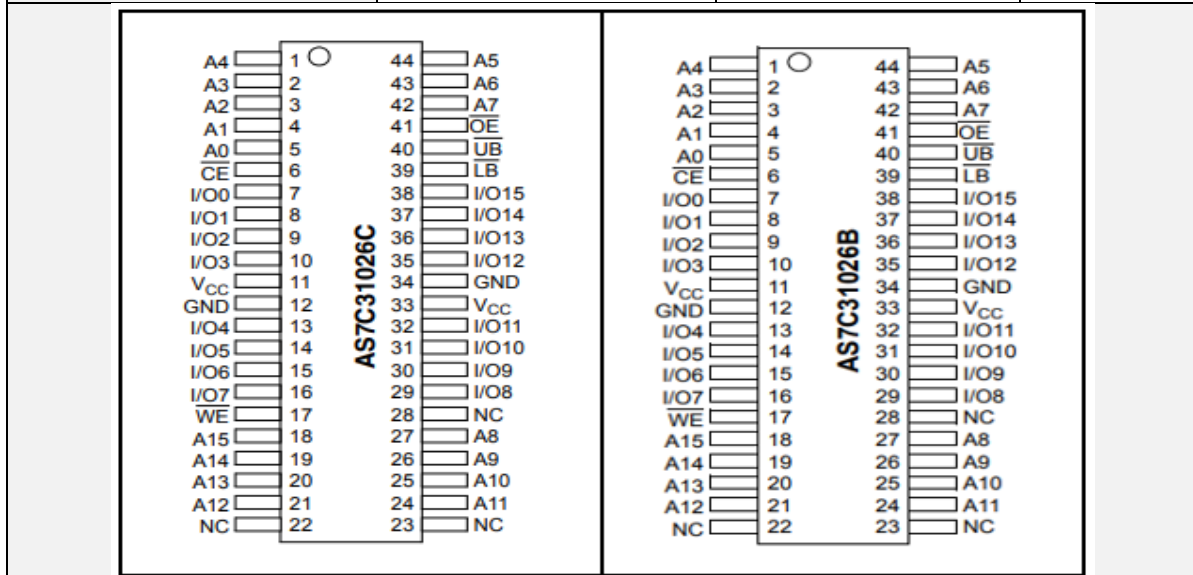
AS7C31025C-12JIN/TR vs AS7C31025B-12JIN/TR Comparison

Parameter	AS7C31025C-12JIN/TR	AS7C31025B-12JIN/TR	Comments
Product Description	FAST ASRAM Rev.C	FAST ASRAM Rev.B	
Capacity / Density	1Mb	1Mb	Same
Memory Organization	128K x 8bits	128K x 8bits	Same
Operating Power Supply	V _{CC} =3.0V ~ 3.6V	V _{CC} =3.0V ~ 3.6V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	C _{in} =6pf, C _{out} =7pf	C _{in} =5pf, C _{out} =7pf	comparable
Read Cycle Time (t _{RC})	12ns (Min.)	12ns (Min.)	Same
Write Cycle Time (t _{WC})	12ns (Min.)	12ns (Min.)	Same
Addr Access Time(t _{AA})	12ns (Max.)	12ns (Max.)	Same
OE Access Time (t _{OE})	6ns (Max.)	6ns (Max.)	Same
V _{OH} (V) @ -4.0mA	2.4 (Min.)	2.4 (Min.)	Same
V _{OL} (V) @ 8mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.0 (Min.)	2.0 (Min.)	Same
V _{IL} (V)	0.8 (Max.)	0.8 (Max.)	Same
I _{LI} / I _{LO} (uA)	5 (Max.)	1 (Max.)	Rev.B better
Operating. Current	I _{CC} = 150mA (Max)	I _{CC} = 65mA (Max.)	Rev.B better
Standby Current I _{sB}	50mA (Max.)	25mA (Max.)	Rev.B better
Standby Current I _{sB1}	10mA (Max.)	5mA (Max.)	Rev.B better
Package	32pin SOJ 400mils	32pin SOJ 400mils	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same



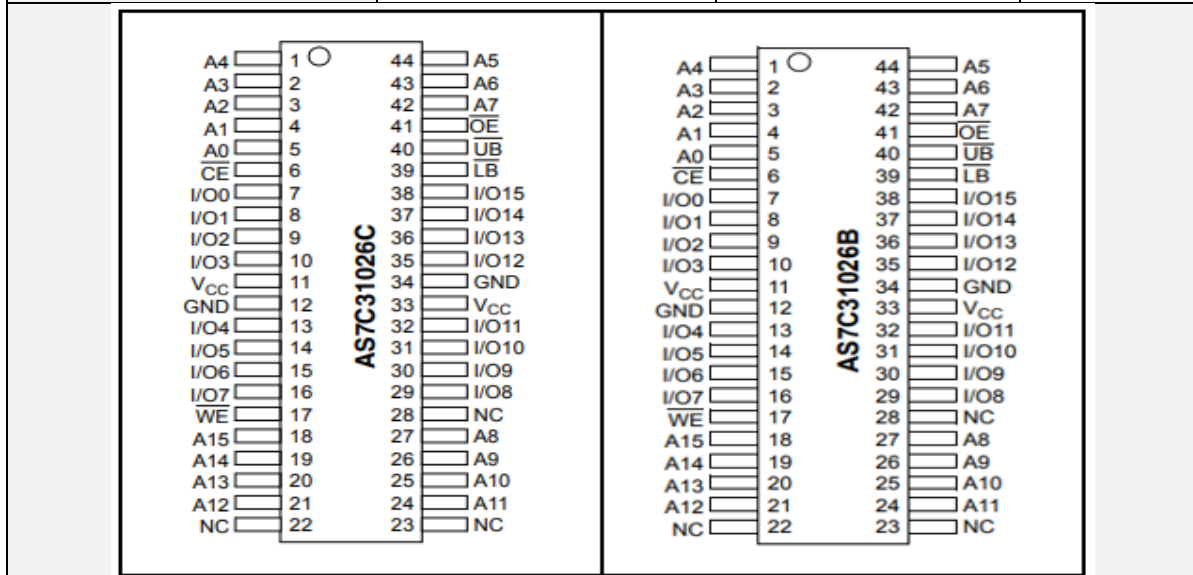
AS7C31026C-12JIN/TR vs AS7C31026B-12JIN/TR Comparison

Parameter \ Part Number & result	AS7C31026C-12JIN/TR	AS7C31026B-12JIN/TR	Comments
Product Description	FAST ASRAM Rev.C	FAST ASRAM Rev.B	
Capacity / Density	1Mb	1Mb	Same
Memory Organization	64K x 16bits	64K x 16bits	Same
Operating Power Supply	$V_{CC}=3.0V \sim 3.6V$	$V_{CC}=3.0V \sim 3.6V$	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	$C_{in}=6pf, C_{out}=7pf$	$C_{in}=5pf, C_{out}=7pf$	comparable
Read Cycle Time (tRC)	12ns (Min.)	12ns (Min.)	Same
Write Cycle Time (tWC)	12ns (Min.)	12ns (Min.)	Same
Addr Access Time(tAA)	12ns (Max.)	12ns (Max.)	Same
OE Access Time (tOE)	6ns (Max.)	6ns (Max.)	Same
$V_{OH}(V)$ @ -4.0mA	2.4 (Min.)	2.4 (Min.)	Same
$V_{OL}(V)$ @ 8mA	0.4 (Max.)	0.4 (Max.)	Same
$V_{IH}(V)$	2.0 (Min.)	2.0 (Min.)	Same
$V_{IL}(V)$	0.8 (Max.)	0.8 (Max.)	Same
$I_{LI} / I_{LO}(\mu A)$	5 (Max.)	1 (Max.)	Rev.B better
Operating. Current	$I_{CC} = 160mA$ (Max)	$I_{CC} = 75mA$ (Max.)	Rev.B better
Standby Current I_{SB}	45mA (Max.)	25mA (Max.)	Rev.B better
Standby Current I_{SB1}	10mA (Max.)	5mA (Max.)	Rev.B better
Package	44pin SOJ 400mils	44pin SOJ 400mils	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same



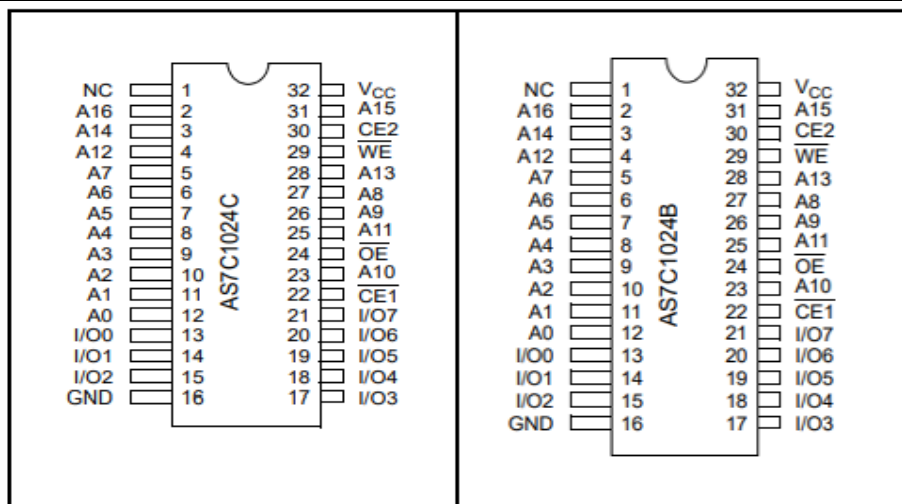
AS7C31026C-12TIN/TR vs AS7C31026B-12TIN/TR Comparison

Parameter \ Part Number & result	AS7C31026C-12TIN/TR	AS7C31026B-12TIN/TR	Comments
Product Description	FAST ASRAM Rev.C	FAST ASRAM Rev.B	
Capacity / Density	1Mb	1Mb	Same
Memory Organization	64K x 16bits	64K x 16bits	Same
Operating Power Supply	$V_{CC}=3.0V \sim 3.6V$	$V_{CC}=3.0V \sim 3.6V$	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	$C_{in}=6pf, C_{out}=7pf$	$C_{in}=5pf, C_{out}=7pf$	comparable
Read Cycle Time (tRC)	12ns (Min.)	12ns (Min.)	Same
Write Cycle Time (tWC)	12ns (Min.)	12ns (Min.)	Same
Addr Access Time(tAA)	12ns (Max.)	12ns (Max.)	Same
OE Access Time (tOE)	6ns (Max.)	6ns (Max.)	Same
$V_{OH}(V)$ @ -4.0mA	2.4 (Min.)	2.4 (Min.)	Same
$V_{OL}(V)$ @ 8mA	0.4 (Max.)	0.4 (Max.)	Same
$V_{IH}(V)$	2.0 (Min.)	2.0 (Min.)	Same
$V_{IL}(V)$	0.8 (Max.)	0.8 (Max.)	Same
$I_{LI} / I_{LO}(\mu A)$	5 (Max.)	1 (Max.)	Rev.B better
Operating. Current	$I_{CC} = 160mA$ (Max)	$I_{CC} = 75mA$ (Max.)	Rev.B better
Standby Current I_{SB}	45mA (Max.)	25mA (Max.)	Rev.B better
Standby Current I_{SB1}	10mA (Max.)	5mA (Max.)	Rev.B better
Package	44pin TSOP II	44pin TSOP II	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same



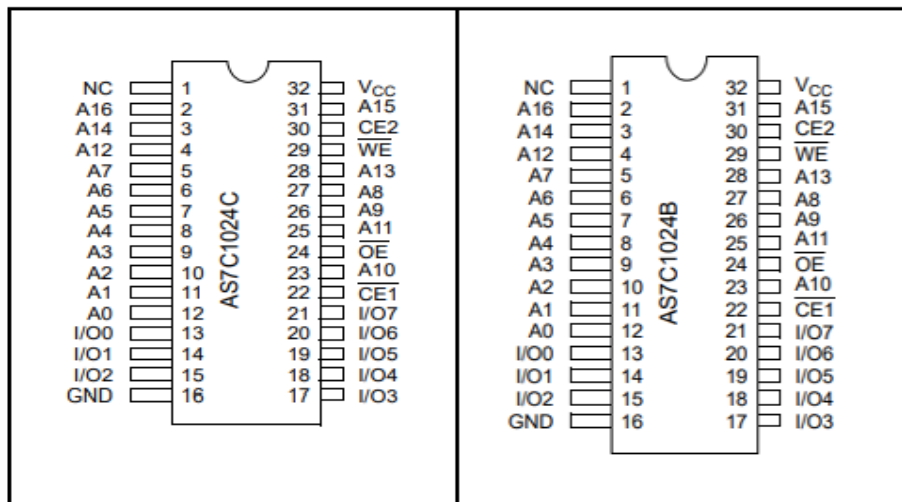
AS7C1024C-12JIN/TR vs AS7C1024B-12JIN/TR Comparison

Parameter	AS7C1024C-12JIN/TR	AS7C1024B-12JIN/TR	Comments
Product Description	FAST ASRAM Rev.C	FAST ASRAM Rev.B	
Capacity / Density	1Mb	1Mb	Same
Memory Organization	128K x 8bits	128K x 8bits	Same
Operating Power Supply	V _{CC} =4.5V ~ 5.5V	V _{CC} =4.5V ~ 5.5V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	C _{in} =7pf, C _{out} =8pf	C _{in} =5pf, C _{out} =7pf	comparable
Read Cycle Time (tRC)	12ns (Min.)	12ns (Min.)	Same
Write Cycle Time (tWC)	12ns (Min.)	12ns (Min.)	Same
Addr Access Time(tAA)	12ns (Max.)	12ns (Max.)	Same
OE Access Time (tOE)	6ns (Max.)	6ns (Max.)	Same
V _{OH} (V) @ -4.0mA	2.4 (Min.)	2.4 (Min.)	Same
V _{OL} (V) @ 8mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.2 (Min.)	2.2 (Min.)	Same
V _{IL} (V)	0.8 (Max.)	0.8 (Max.)	Same
I _{LI} / I _{LO} (uA)	5 (Max.)	1 (Max.)	Rev.B better
Operating. Current	I _{CC} = 160mA (Max)	I _{CC} = 100mA (Max.)	Rev.B better
Standby Current I _{SB}	40mA (Max.)	45mA (Max.)	Comparable
Standby Current I _{SB1}	10mA (Max.)	10mA (Max.)	Same
Package	32pin SOJ (400mils)	32pin SOJ (400mils)	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same



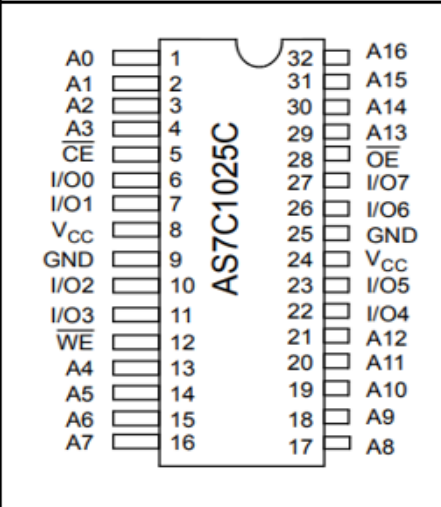
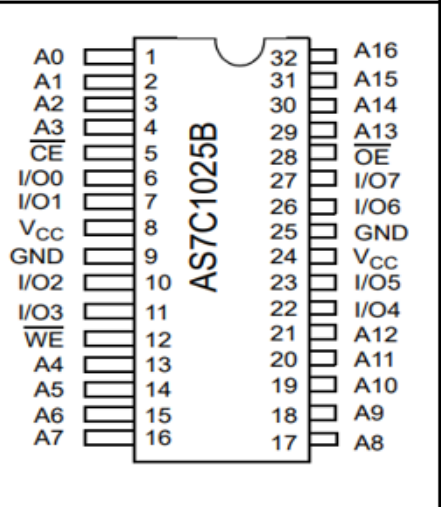
AS7C1024C-12TJIN/TR vs AS7C1024B-12TJIN/TR Comparison

Parameter	AS7C1024C-12TJIN/TR	AS7C1024B-12TJIN/TR	Comments
Product Description	FAST ASRAM Rev.C	FAST ASRAM Rev.B	
Capacity / Density	1Mb	1Mb	Same
Memory Organization	128K x 8bits	128K x 8bits	Same
Operating Power Supply	V _{CC} = 4.5V ~ 5.5V	V _{CC} = 4.5V ~ 5.5V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	C _{in} =7pf, C _{out} =8pf	C _{in} =5pf, C _{out} =7pf	comparable
Read Cycle Time (t _{RC})	12ns (Min.)	12ns (Min.)	Same
Write Cycle Time (t _{WC})	12ns (Min.)	12ns (Min.)	Same
Addr Access Time(t _{AA})	12ns (Max.)	12ns (Max.)	Same
OE Access Time (t _{OE})	6ns (Max.)	6ns (Max.)	Same
V _{OH} (V) @ -4.0mA	2.4 (Min.)	2.4 (Min.)	Same
V _{OL} (V) @ 8mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.2 (Min.)	2.2 (Min.)	Same
V _{IL} (V)	0.8 (Max.)	0.8 (Max.)	Same
I _{LI} / I _{LO} (uA)	5 (Max.)	1 (Max.)	Rev.B better
Operating. Current	I _{CC} = 160mA (Max)	I _{CC} = 100mA (Max.)	Rev.B better
Standby Current I _{SB}	40mA (Max.)	45mA (Max.)	Comparable
Standby Current I _{SB1}	10mA (Max.)	10mA (Max.)	Same
Package	32pin SOJ (300mils)	32pin SOJ (300mils)	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same



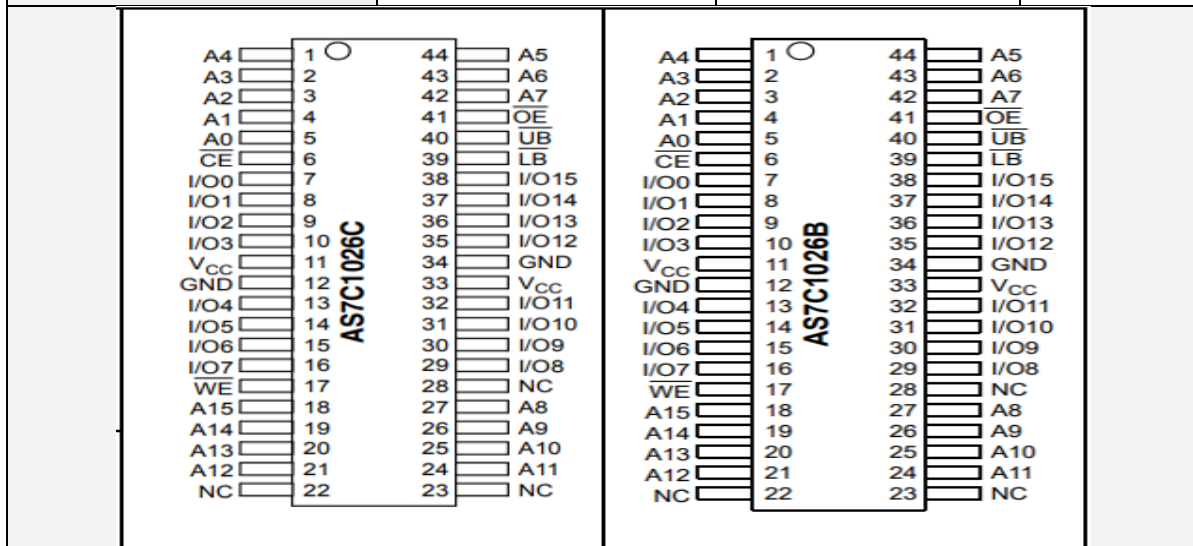
AS7C1025C-15JIN/TR vs AS7C1025B-15JIN/TR Comparison

Parameter	AS7C1025C-15JIN/TR	AS7C1025B-15JIN/TR	Comments
Product Description	FAST ASRAM Rev.C	FAST ASRAM Rev.B	
Capacity / Density	1Mb	1Mb	Same
Memory Organization	128K x 8bits	128K x 8bits	Same
Operating Power Supply	V _{CC} = 4.5V ~ 5.5V	V _{CC} = 4.5V ~ 5.5V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	C _{in} = C _{out} = 8pf	C _{in} = 5pf, C _{out} = 7pf	Comparable
Read Cycle Time (t _{RC})	15ns (Min.)	15ns (Min.)	Same
Write Cycle Time (t _{WC})	15ns (Min.)	15ns (Min.)	Same
Addr Access Time (t _{AA})	15ns (Max.)	15ns (Max.)	Same
OE Access Time (t _{OE})	6ns (Max.)	7ns (Max.)	Comparable
V _{OH} (V) @ -4.0mA	2.4 (Min.)	2.4 (Min.)	Same
V _{OL} (V) @ 8mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.2 (Min.)	2.2 (Min.)	Same
V _{IL} (V)	0.8 (Max.)	0.8 (Max.)	Same
I _{LI} / I _{LO} (uA)	5 (Max.)	1 (Max.)	Rev.B better
Operating. Current	I _{CC} = 160mA (Max)	I _{CC} = 90mA (Max.)	Rev.B better
Standby Current I _{SB}	40mA (Max.)	45mA (Max.)	Comparable
Standby Current I _{SB1}	10mA (Max.)	10mA (Max.)	Same
Package	32pin SOJ (400mils)	32pin SOJ (400mils)	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same

 <p>AS7C1025C</p>	 <p>AS7C1025B</p>
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AS7C1026C-15JIN/TR vs AS7C1026B-15JIN/TR Comparison

Parameter	AS7C1026C-15JIN/TR	AS7C1026B-15JIN/TR	Comments
Product Description	FAST ASRAM Rev.C	FAST ASRAM Rev.B	
Capacity / Density	1Mb	1Mb	Same
Memory Organization	64K x 16bits	64K x 16bits	Same
Operating Power Supply	V _{CC} =4.5V ~ 5.5V	V _{CC} =4.5V ~ 5.5V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Same
I/O Capacitance	C _{in} = 6pf, C _{out} =7pf	C _{in} =5pf, C _{out} =7pf	Comparable
Read Cycle Time (t _{RC})	15ns (Min.)	15ns (Min.)	Same
Write Cycle Time (t _{WC})	15ns (Min.)	15ns (Min.)	Same
Addr Access Time(t _{AA})	15ns (Max.)	15ns (Max.)	Same
OE Access Time (t _{OE})	7ns (Max.)	7ns (Max.)	Same
V _{OH} (V) @ -4.0mA	2.4 (Min.)	2.4 (Min.)	Same
V _{OL} (V) @ 8mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.2 (Min.)	2.2 (Min.)	Same
V _{IL} (V)	0.8 (Max.)	0.8 (Max.)	Same
I _{LI} / I _{LO} (uA)	5 (Max.)	1 (Max.)	Rev.B better
Operating. Current	I _{CC} = 210mA (Max)	I _{CC} = 90mA (Max.)	Rev.B better
Standby Current I _{SB}	60mA (Max.)	45mA (Max.)	Rev.B better
Standby Current I _{SB1}	10mA (Max.)	10mA (Max.)	Same
Package	44pin SOJ (400mils)	44pin SOJ (400mils)	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same



AS7C1026C-15TIN/TR vs AS7C1026B-15TCN/TR Comparison

Parameter	AS7C1026C-15TIN/TR	AS7C1026B-15TCN/TR	Comments
Product Description	FAST ASRAM Rev.C	FAST ASRAM Rev.B	
Capacity / Density	1Mb	1Mb	Same
Memory Organization	64K x 16bits	64K x 16bits	Same
Operating Power Supply	V _{CC} = 4.5V ~ 5.5V	V _{CC} = 4.5V ~ 5.5V	Same
Operating Temperature	Industrial (-40°C to 85°C)	Commercial (0°C to 70°C)	Different
I/O Capacitance	C _{in} = 6pf, C _{out} = 7pf	C _{in} = 5pf, C _{out} = 7pf	Comparable
Read Cycle Time (t _{RC})	15ns (Min.)	15ns (Min.)	Same
Write Cycle Time (t _{WC})	15ns (Min.)	15ns (Min.)	Same
Addr Access Time (t _{AA})	15ns (Max.)	15ns (Max.)	Same
OE Access Time (t _{OE})	7ns (Max.)	7ns (Max.)	Same
V _{OH} (V) @ -4.0mA	2.4 (Min.)	2.4 (Min.)	Same
V _{OL} (V) @ 8mA	0.4 (Max.)	0.4 (Max.)	Same
V _{IH} (V)	2.2 (Min.)	2.2 (Min.)	Same
V _{IL} (V)	0.8 (Max.)	0.8 (Max.)	Same
I _{LI} / I _{LO} (uA)	5 (Max.)	1 (Max.)	Rev.B better
Operating. Current	I _{CC} = 210mA (Max)	I _{CC} = 90mA (Max.)	Rev.B better
Standby Current I _{SB}	60mA (Max.)	45mA (Max.)	Rev.B better
Standby Current I _{SB1}	10mA (Max.)	10mA (Max.)	Same
Package	44pin TSOP II	44pin TSOP II	Same
Package Material	Pb and Halogen Free		Same
Pin to Pin Compatible	Yes	Yes	Same

